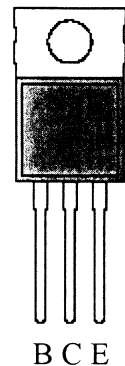


2SC2166

Silicon NPN Transistor

Final RF Power Output

The 2SC2166 is a silicon NPN epitaxial planer type transistor designed for RF power amplifiers on HF band mobile radio applications.



Features:

- High Power Gain: $G_{pe} \geq 13,8\text{dB}$ ($V_{CC} = 12\text{V}$, $P_O = 6\text{W}$, $f = 27\text{MHz}$)

Application:

- 3 to 4 Watt Output Power Class AB Amplifier Applications in HF Band

Absolute Maximum Ratings: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Collector-Emitter Voltage ($R_{BE} = \text{Infinity}$), V_{CEO}	75V
Collector-Base Voltage, V_{CBO}	75V
Emitter-Base Voltage, V_{EBO}	5V
Collector Current, I_C	4A
Collector Power Dissipation ($T_A = +25^\circ\text{C}$), P_D	1.5W
Collector Power Dissipation ($T_C = +50^\circ\text{C}$), P_D	12,5W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C
Thermal Resistance, Junction-to-Case, R_{thJC}	10°C/W
Thermal Resistance, Junction-to-Ambient, R_{thJA}	83°C/W

